

**Silicon NPN Power Transistors**

**2SC2579**

**DESCRIPTION**

- With TO-3PN package
- High power dissipation
- High current capability

**APPLICATIONS**

- For audio frequency power amplifier applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

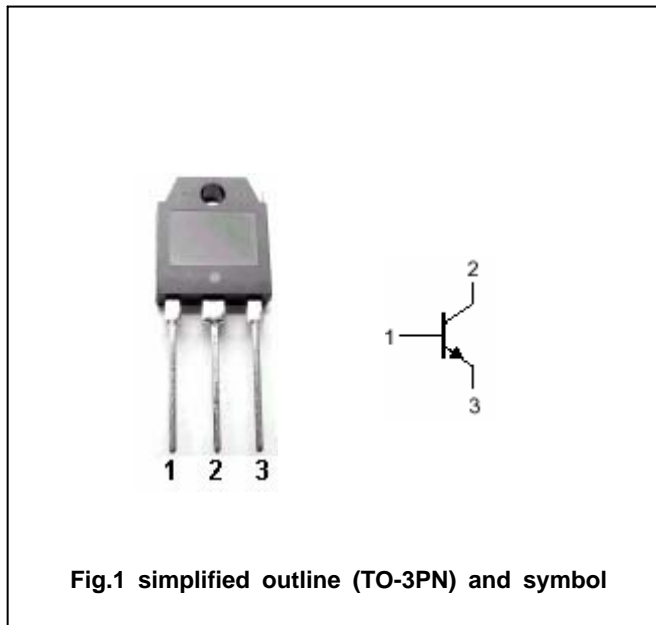


Fig.1 simplified outline (TO-3PN) and symbol

**Absolute maximum ratings(Ta= )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	160	V
$V_{CEO}$	Collector-emitter voltage	Open base	160	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		8	A
$P_C$	Collector power dissipation	$T_C=25$	80	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =5mA; I <sub>E</sub> =0	160			V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA; R <sub>BE</sub> =	160			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =5mA; I <sub>C</sub> =0	6			V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =160V; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =3A; V <sub>CE</sub> =4V	50			
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =0.5A			2.0	V
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A; V <sub>CE</sub> =10V		20		MHz

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PACKAGE OUTLINE

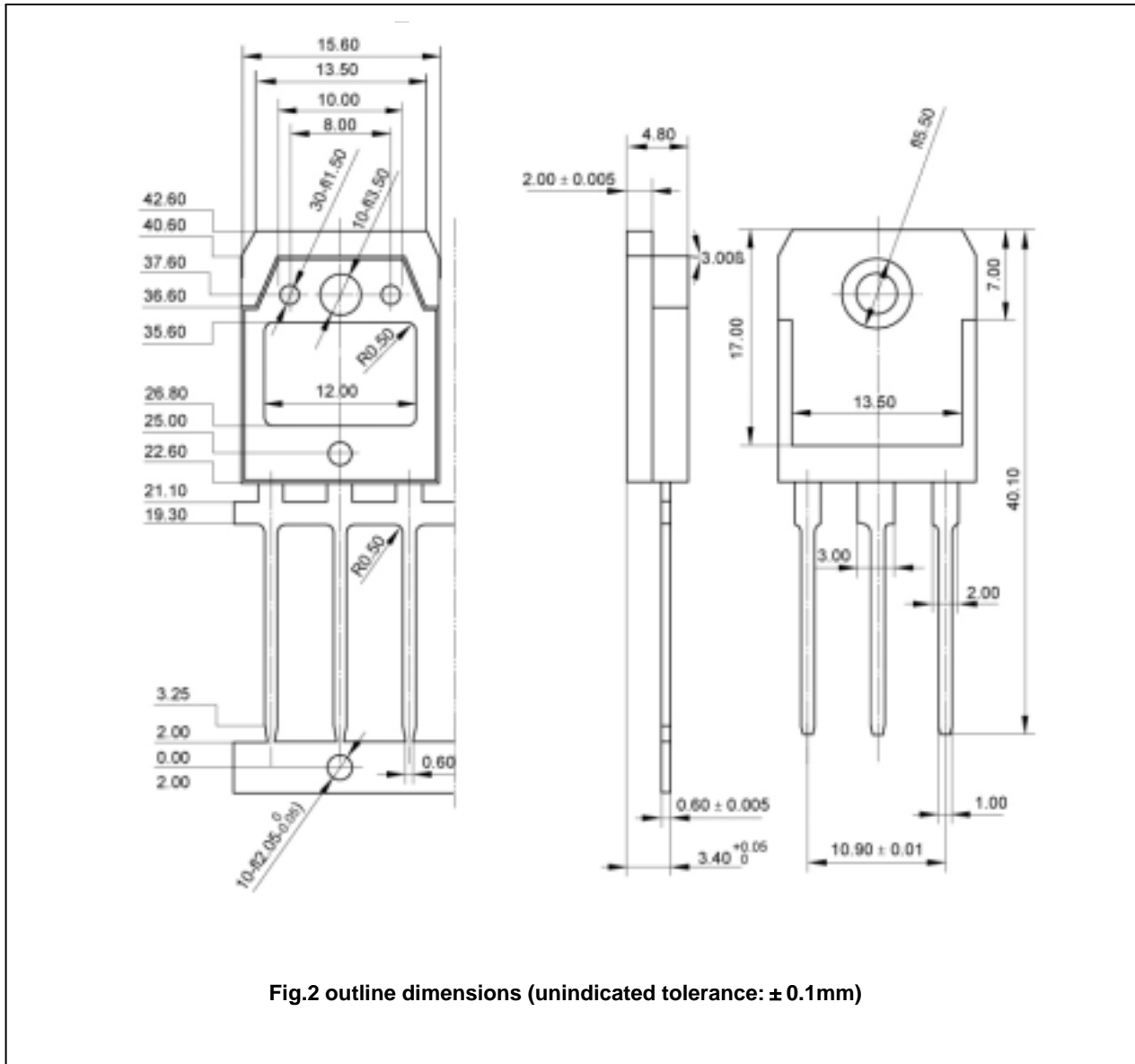


Fig.2 outline dimensions (unindicated tolerance:  $\pm 0.1\text{mm}$ )